LSIC2SD065C08A 650 V, 8 A SiC Schottky Barrier Diode









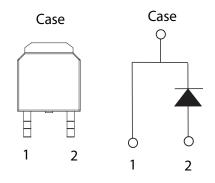
Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-252-2L (DPAK)



Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V	
DC Blocking Voltage	V _R	T _J = 25 °C	650	V	
		T _C = 25 °C	23		
Continuous Forward Current	l _F	T _C = 135 °C	10.7	А	
		T _C = 150 °C	8		
Non-Repetitive Forward Surge Current	I _{FSM}	$T_{\rm C} = 25 {\rm ^{\circ}C}$, $T_{\rm P} = 10 {\rm ms}$, Half sine pulse	40	А	
Power Dissipation	D	T _C = 25 °C	88	W	
rower dissipation	P_{Tot}	T _C = 110 °C	38		
Operating Junction Temperature	T _J	-	-55 to 175	°C	
Storage Temperature	T _{STG}	-	-55 to 150	°C	
Soldering Temperature (reflow MSL1)	T _{sold}	-	260	°C	

Electrical Characteristics

			Value				
Characteristics	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Forward Voltage	\/	I _F = 8 A, T _J = 25 °C	-	1.5	1.8	V	
Forward voitage	V _F	I _F = 8 A, T _J = 175 °C	-	1.85	-		
Reverse Current I _R	$V_{R} = 650 V$, $T_{J} = 25 ^{\circ}C$	-	<1	50	^		
	I _R	$V_{R} = 650 \text{V}, T_{J} = 175 ^{\circ}\text{C}$	-	15	-	μΑ	
Total Capacitance C		$V_R = 1 V$, $f = 1 MHz$	-	415	-		
	С	$V_R = 200 V$, $f = 1 MHz$	-	56	-	рF	
		$V_R = 400 \text{V}, \text{f} = 1 \text{MHz}$	-	41	-		
Total Capacitive Charge	Q _c	$V_R = 400 \text{ V, } Q_C = \int\limits_0^{V_R} C(V) dV$	-	29	-	nC	

Footnote: T_J = +25 °C unless otherwise specified

Thermal Characteristics						
Characteristics	Symbol	Value	Unit			
Thermal Resistance	R _{esc}	1.7	°C/W			

Figure 1: Typical Foward Characteristics

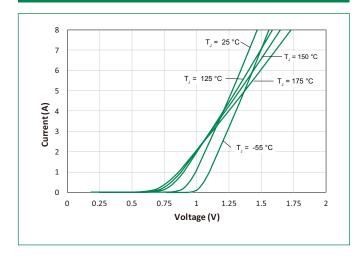


Figure 2: Typical Reverse Characteristics

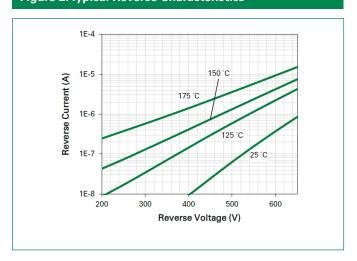




Figure 3: Power Derating

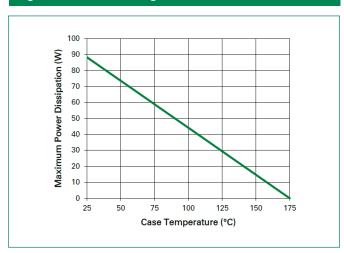


Figure 4: Current Derating

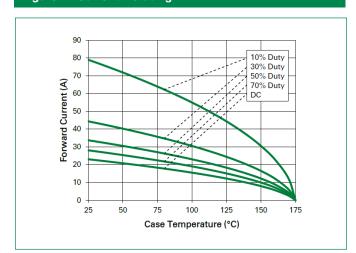


Figure 5: Capacitance vs. Reverse Voltage

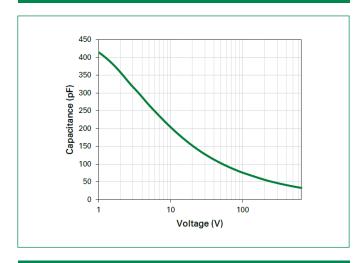


Figure 6: Capacitive Charge vs. Reverse Voltage

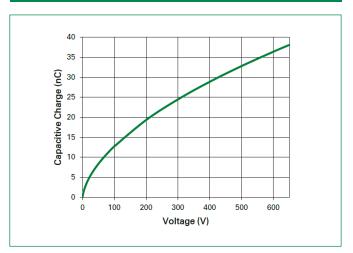


Figure 7: Stored Energy vs. Reverse Voltage

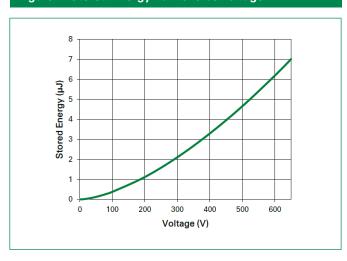
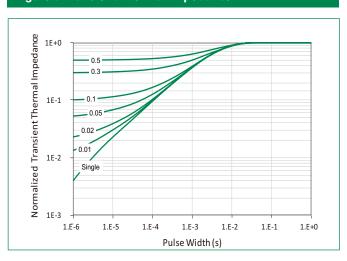
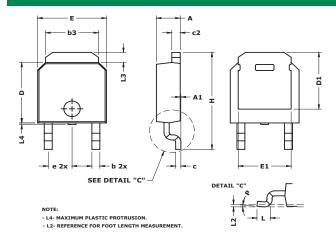


Figure 8: Transient Thermal Impedance

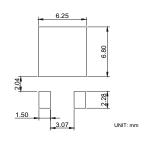




Dimensions TO-252-2L (DPAK)

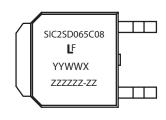


Recommended Solder Pattern Layout



Symbol	Inches			Millimeters		
Зуппрог	Min	Nom	Max	Min	Nom	Max
Α	0.085	0.090	0.095	2.16	2.29	2.41
A1	0	0.003	0.005	0	0.08	0.13
b	0.025	0.030	0.035	0.64	0.76	0.89
b3	0.195	0.200	0.215	4.95	5.08	5.46
С	0.018	0.020	0.024	0.46	0.51	0.61
C2	0.018	0.032	0.035	0.46	0.81	0.89
D	0.235	0.240	0.245	5.97	6.10	6.22
D1	0.205	-	-	5.21	-	-
Е	0.250	0.260	0.265	6.35	6.60	6.73
E1	0.170	-	-	4.32	-	-
е	C	.090 BSC		2.29 BSC		
Н	0.370	0.387	0.410	9.40	9.83	10.41
L	0.040	0.045	0.050	1.02	1.14	1.27
L2	0.010 BSC			0.25 BSC		
L3	0.035	-	0.050	0.89	-	1.27
L4	0	-	0.006	0	-	0.15
Р	0°	-	8°	0°	-	8°

Part Numbering and Marking System



SIC = SiC Diode = Gen2 = Schottky Diode SD 065 = Voltage Rating (650 V) С = TO-252-2L (DPAK) = Current Rating (8 Å) 80 ΥY = Year $\mathsf{W}\mathsf{W}$ = Week = Special code

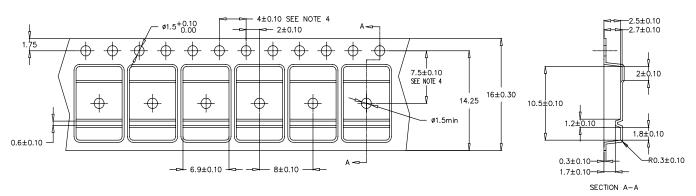
ZZZZZZ-ZZ = Lot Number

Packing Options

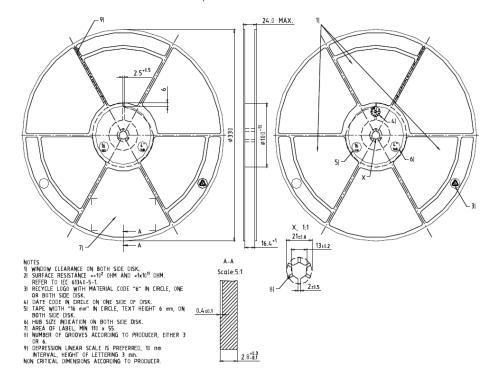
Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065C08A	SIC2SD065C08	Tape and Reel	2500



Carrier Tape & Reel Specification TO-252-2L (DPAK)



- Material: Black Conductive Polysterene
 10 sprocket hole pitch cumulative tolerance ± 0.20
 3. Camber not to exceed 1 mm in 100 mm.
 4 Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.
- 5. Device orientation: TRL (leads perpendicular to the sprocket)
- 6. General tolerance is \pm 0.10 mm unless otherwise specified.



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